

# *Interconnect Extraction and Analysis in High-Frequency, Sub-Micron, Digital VLSI Design*

**Peter Feldmann**

**Bell Labs/Lucent Technologies, Murray Hill, NJ**

**Roland W. Freund**

**Bell Labs/Lucent Technologies, Murray Hill, NJ**

**Tak Young**

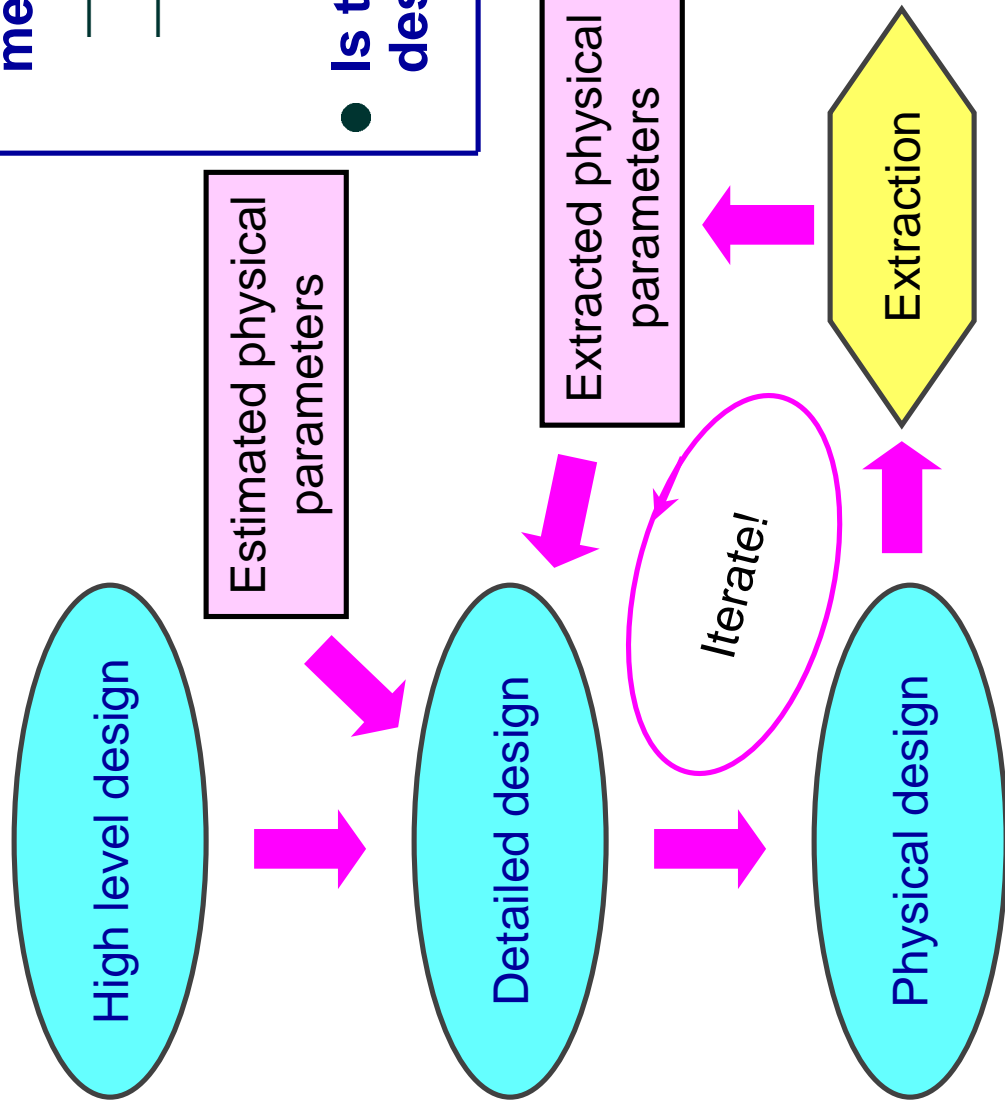
**Synopsys Inc., Mountain View, CA**

# *General outline*

- **Technology trends**
- **Practical RC extraction techniques**
- **Fundamental extraction algorithms**
- **Linear Model Reduction Techniques**
- **Role of extraction in the VLSI design flow**
- **Conclusion and outlook**

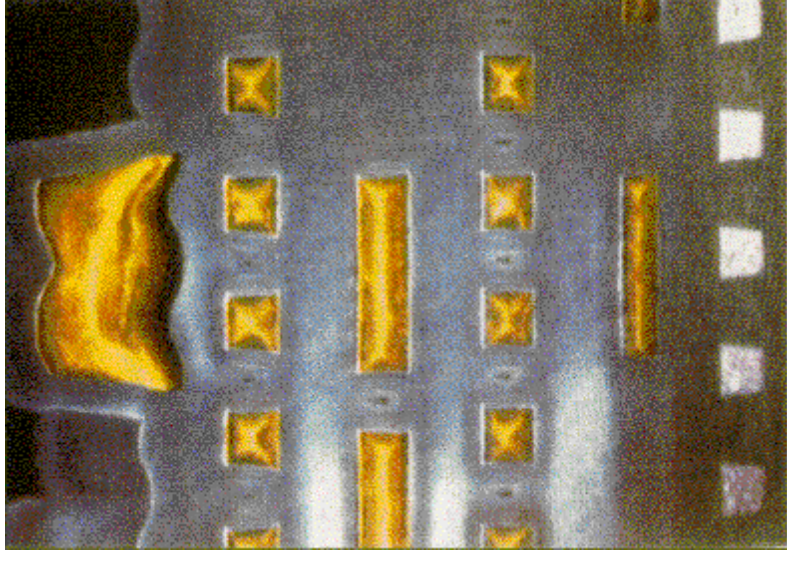
# VLSI design methodology

- Traditional design methodology
  - functionality first
  - interconnect considered “parasitics”
- Is this still the right way to design?



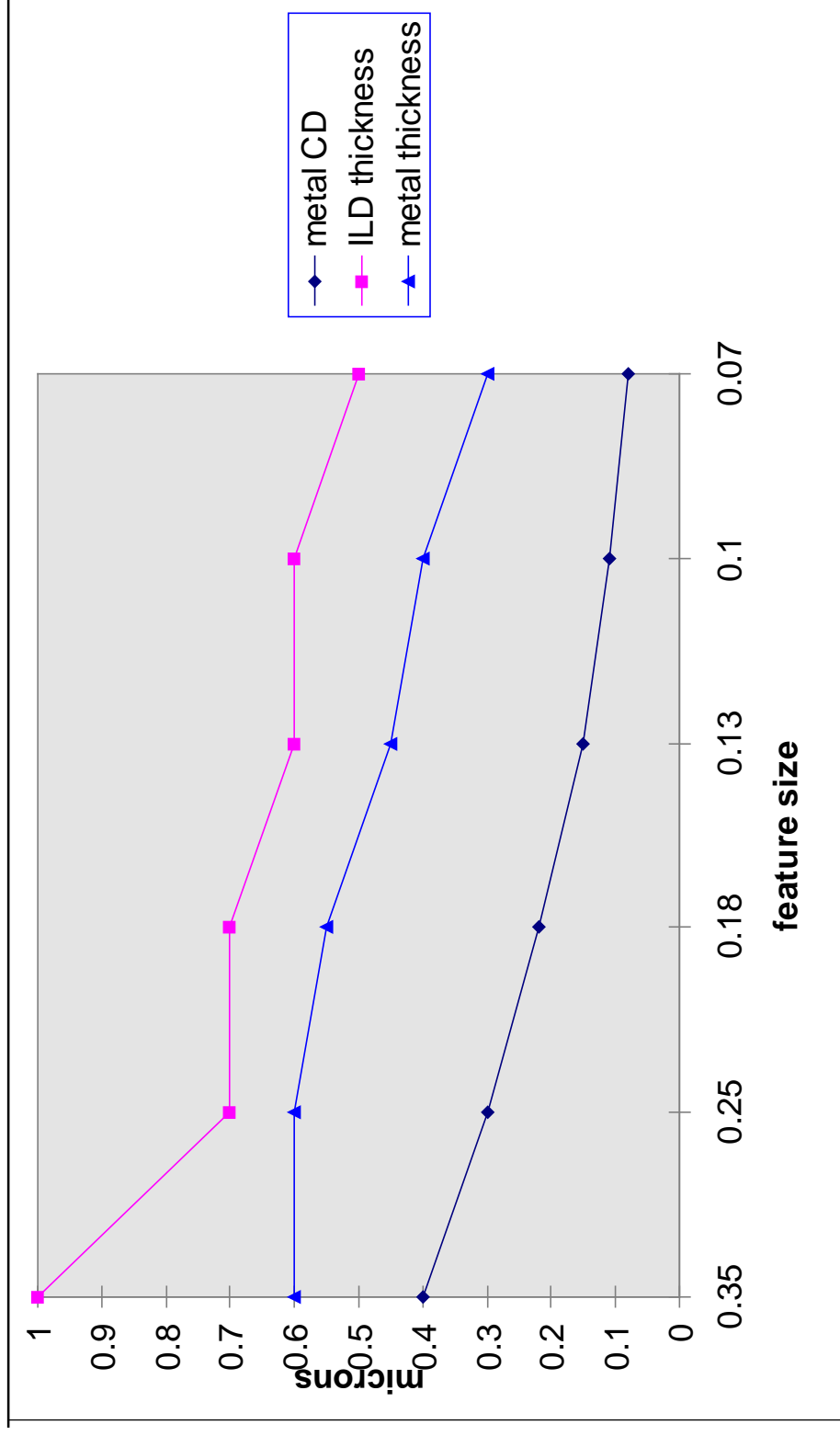
# VLSI interconnect trends

- **Scaling Trends**
  - smaller feature size
  - increase of chip size
  - affected physical parameters
    - decrease of metal width/spacing
    - decrease of dielectric thickness
    - decrease of metal thickness
    - increase of interconnect length
  - increase in operating frequency
  - increase in chip complexity
- **Impact on Electrical Parameters**
  - capacitance
    - increase of total capacitance
    - coupling increasingly dominant
  - increase of interconnect resistance
  - inductance effects felt at chip-level



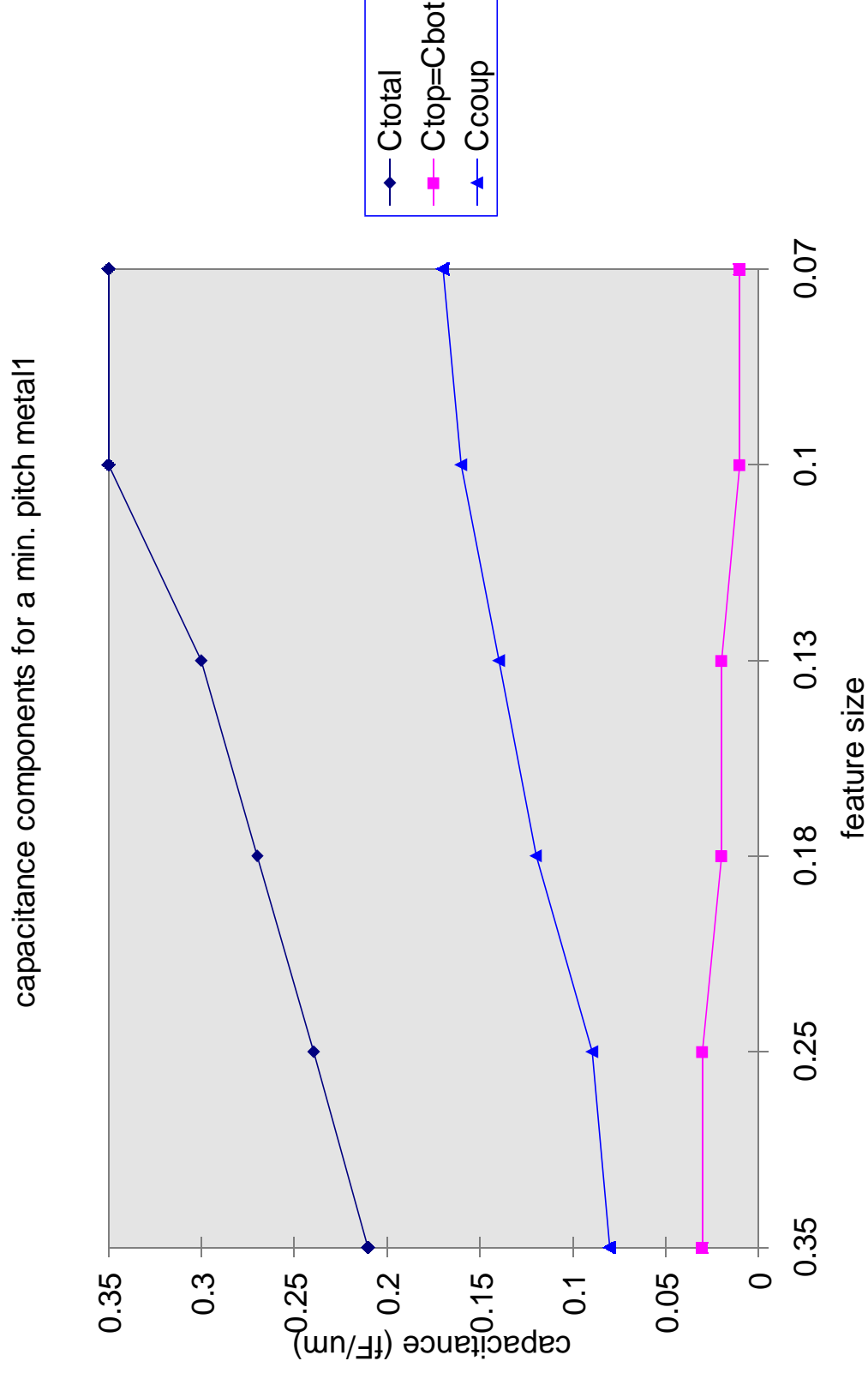
SEM picture courtesy of IBM Corp.  
© Copyright IBM Corp. 1994, 1996, 1998.  
All rights reserved.

# Metal interconnect scaling



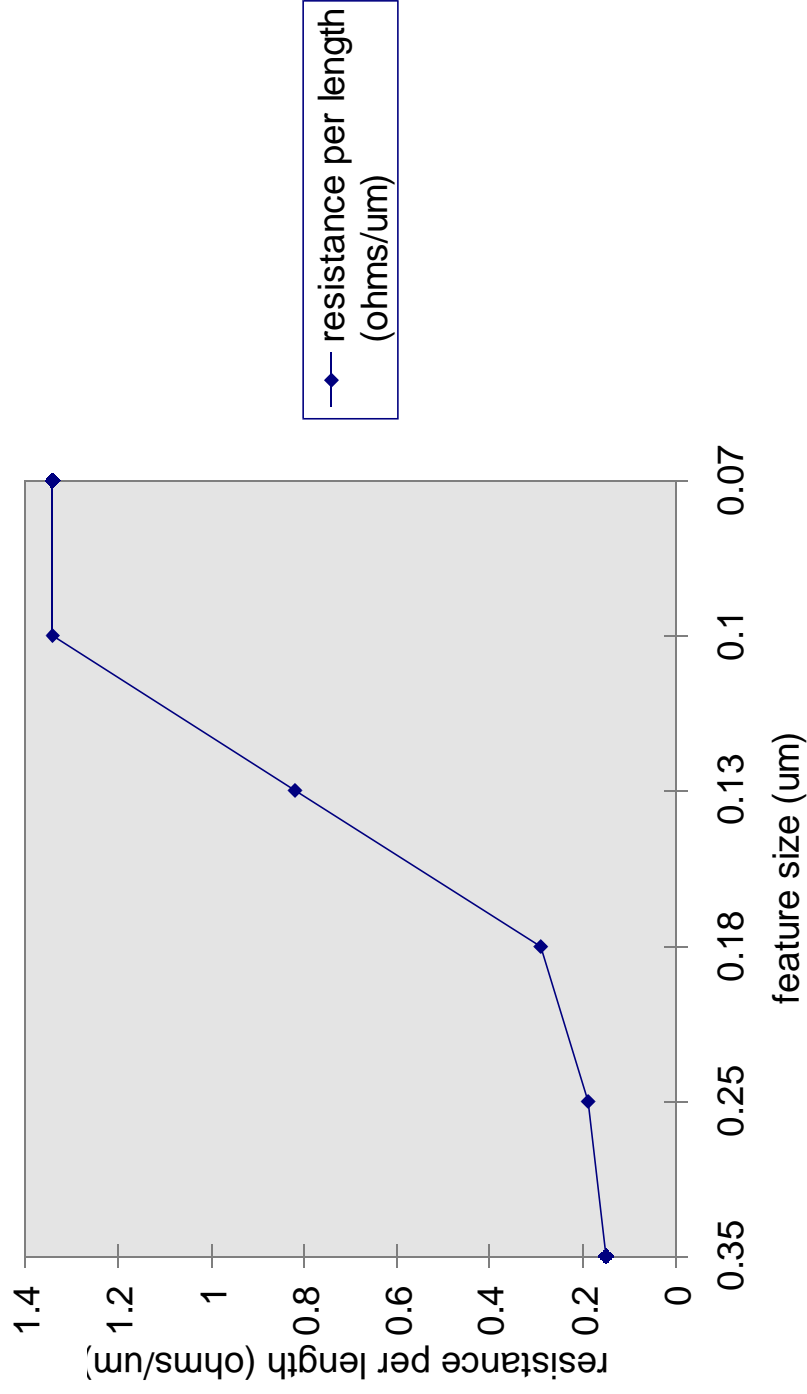
CD: critical dimension      ILD: interlayer dielectric

# Capacitance scaling

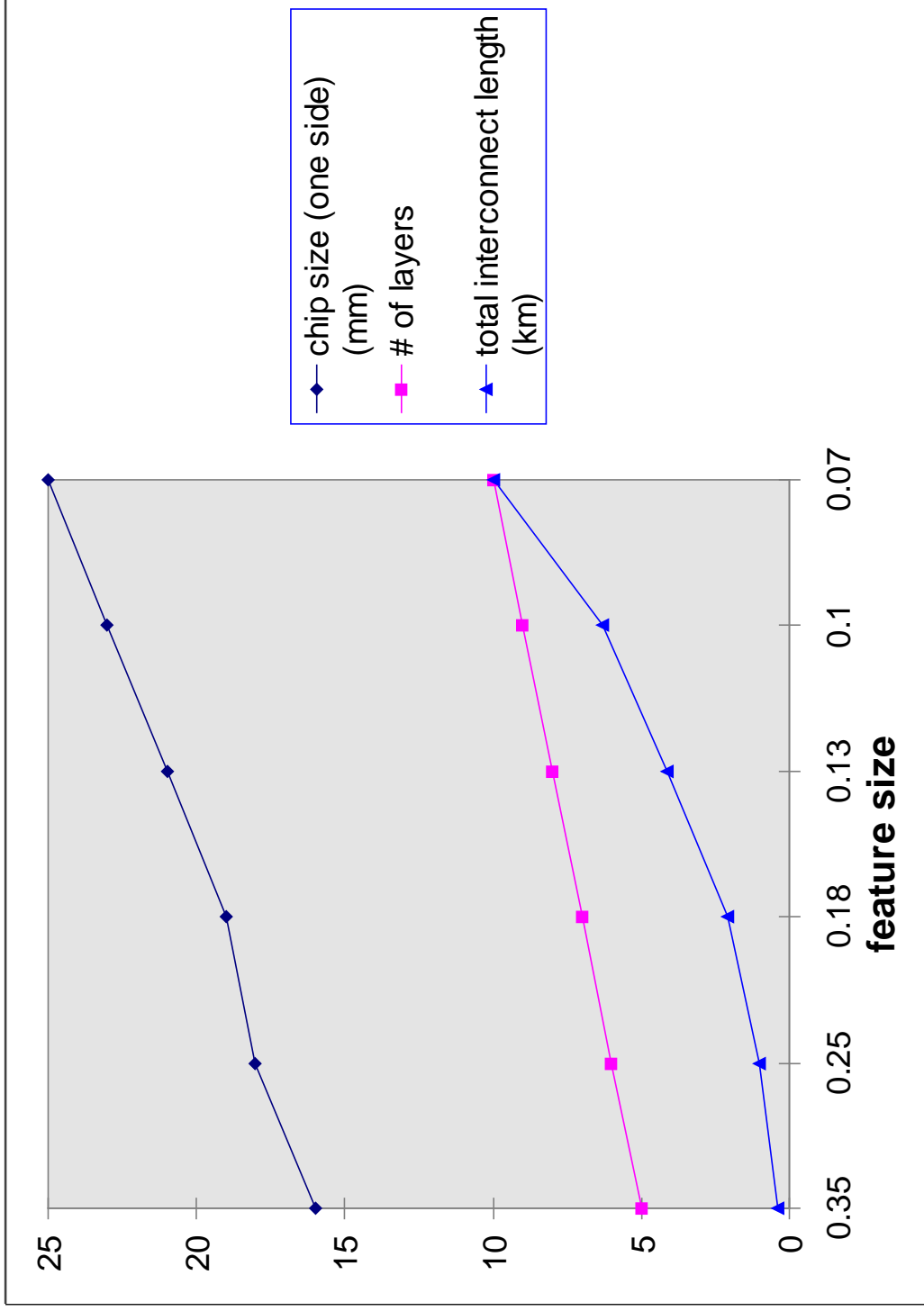


# Resistance scaling

resistance per length of a min. pitch metal 1 (ohms/um)

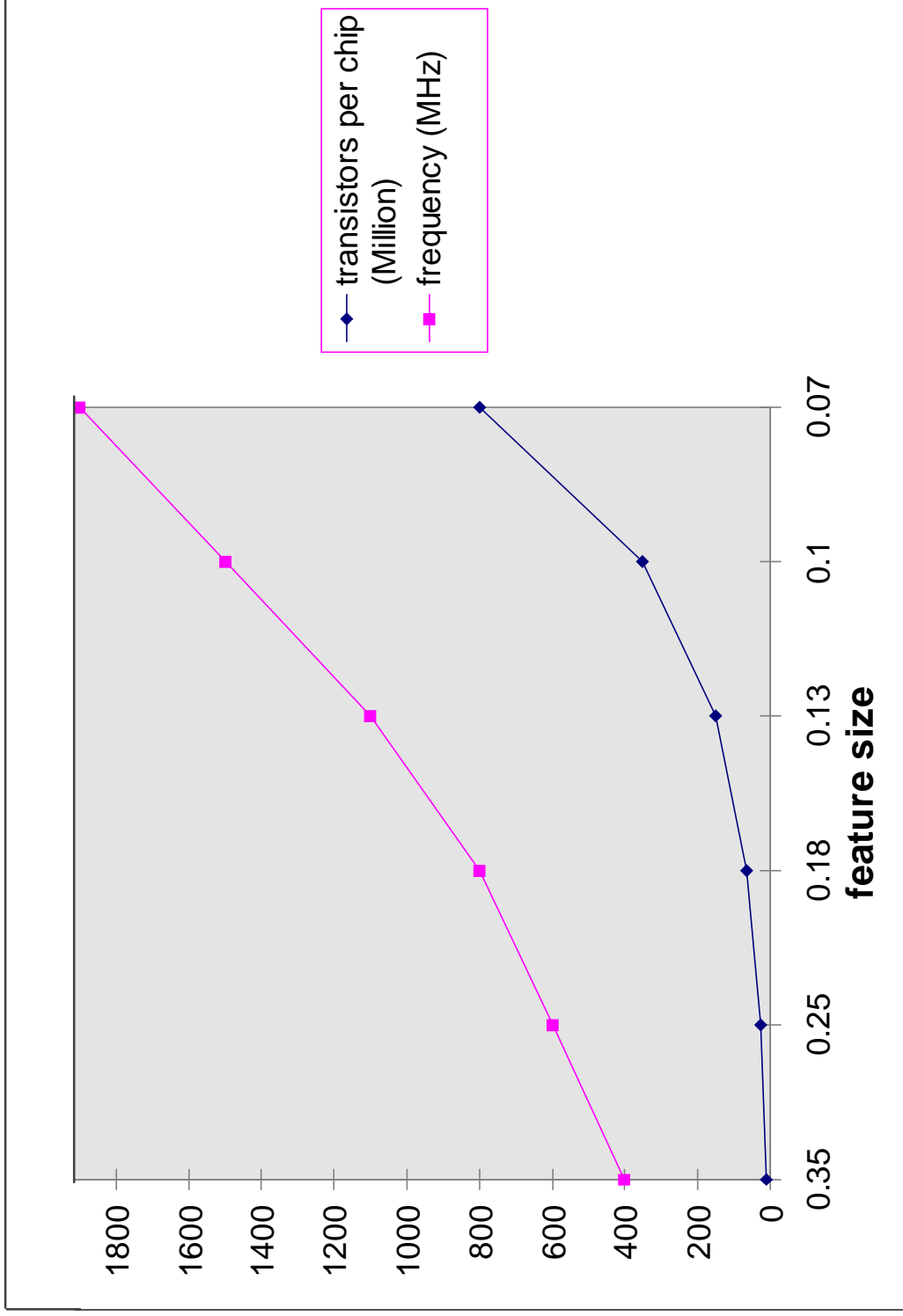


# Chip evolution





# Chip speed and complexity



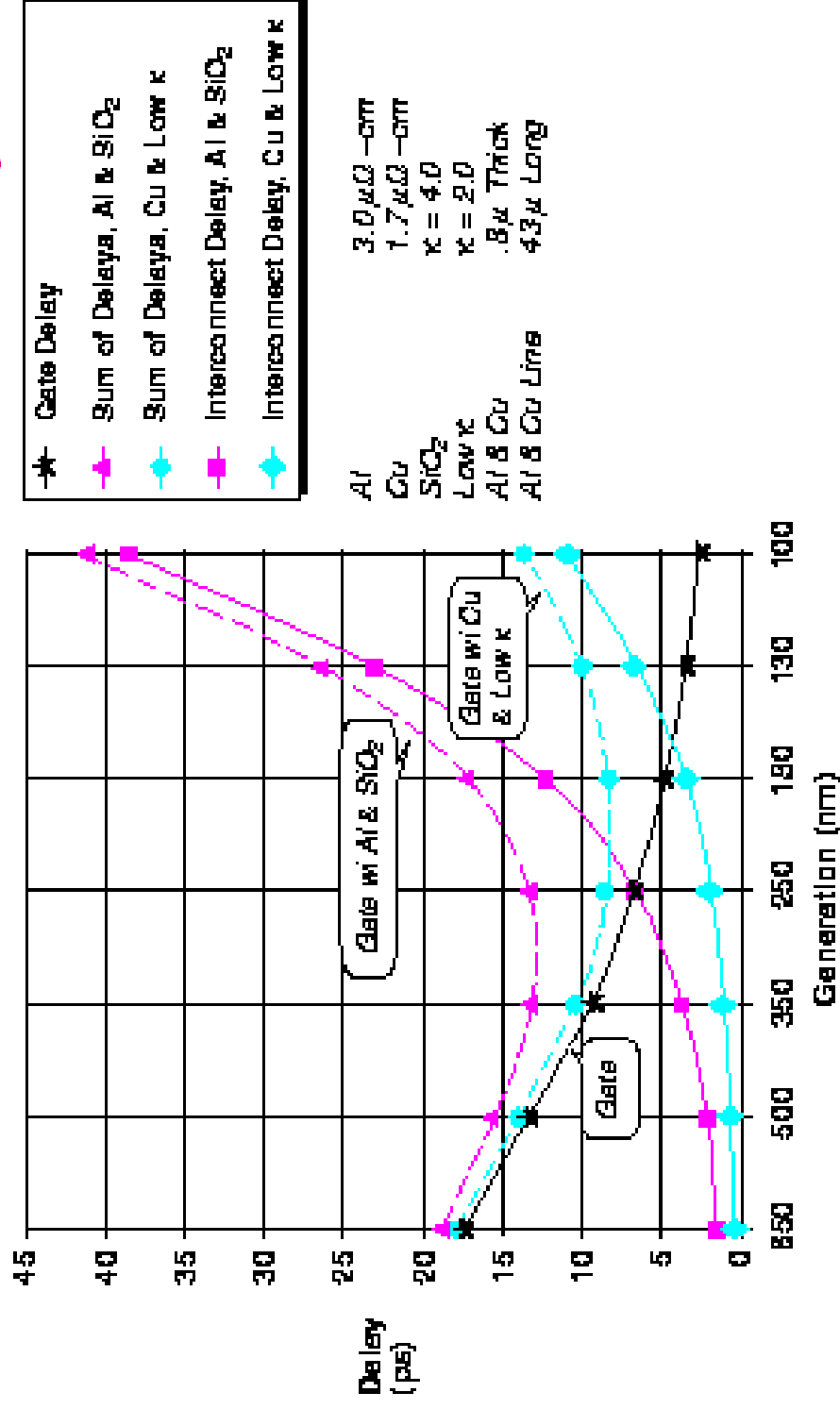
# Technology Solutions

- **Process Technology Solutions**
  - increase in # of layers => shorter interconnect
  - Higher conductivity => lower resistance  $R \propto \frac{1}{\sigma}$   
Copper
  - Low dielectric constant => low capacitance  $C \propto \epsilon$   
Low-K materials (e.g., polyimide)
  - planarization

# *Impact of interconnect on design*

- **Signal Delay**
  - Impact of wire capacitance, resistance, and length
  - Impact of adjacent signals through cross-talk
- **Signal Integrity**
  - False switching due to cross-talk
- **Reliability**
  - Increasing current drive may cause electromigration
  - Cross-talk may induce signal levels outside supply levels

# Gate vs. interconnect delay



● Despite everything interconnect effects dominate!

# Wirelength distribution

